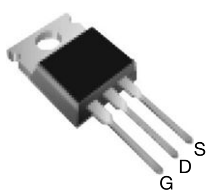
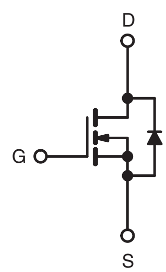
Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	500	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	0.85
Q_g (Max.) (nC)	39	
Q_{gs} (nC)	10	
Q_{gd} (nC)	19	
Configuration	Single	

TO-220AB





N-Channel MOSFET

FEATURES

- Ultra Low Gate Charge
- Reduced Gate Drive Requirement
- Enhanced 30 V V_{GS} Rating
- Reduced C_{iss}, C_{oss}, C_{rss}
- Extremely High Frequency Operation
- Repetitive Avalanche Rated
- Compliant to RoHS Directive 2002/95/EC

Pb Available

RoHS* COMPLIANT

DESCRIPTION

This new series of low charge Power MOSFETs achieve signiticantly lower gate charge over conventional MOSFETs. Utilizing the new LCDMOS technology, the device improvements are achieved without added product cost, allowing for reduced gate drive requirements and total system savings. In addition, reduced switching losses and improved efficiency are achievable in a variety of high frequency applications. Frequencies of a few MHz at high current are possible using the new low charge MOSFETs.

These device improvements combined with the proven ruggedness and reliability that are characteristic of Power MOSFETs offer the designer a new standard in power transistors for switching applications.

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRF840LCPbF
	SiHF840LC-E3
SnPb	IRF840LC
	SiHF840LC

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

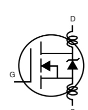
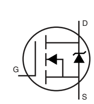
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	500	V
Gate-Source Voltage			V_{GS}	± 30	
Continuous Drain Current	V_{GS} at 10 V	T_C = 25 °C	I_D	8.0	A
		T_C = 100 °C		5.1	
Pulsed Drain Current[a]			I_{DM}	28	
Linear Derating Factor				1.0	W/°C
Single Pulse Avalanche Energy[b]			E_{AS}	510	mJ
Repetitive Avalanche Current[a]			I_{AR}	8.0	A
Repetitive Avalanche Energy[a]			E_{AR}	13	mJ
Maximum Power Dissipation	T_C = 25 °C		P_D	125	W
Peak Diode Recovery dV/dt[c]			dV/dt	3.5	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300[d]	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. V_{DD} = 50 V, starting T_J = 25 °C, L = 14 mH, R_g = 25 Ω, I_{AS} = 8.0 A (see fig. 12).
c. $I_{SD} \leq$ 8.0 A, dI/dt $\leq$ 100 A/μs, $V_{DD} \leq V_{DS}$, $T_J \leq$ 150 °C.
d. 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.0	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA	500	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA	-	0.63	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 500 V, V_{GS} = 0 V	-	-	25	μA
		V_{DS} = 400V, V_{GS} = 0 V, T_J = 125 °C	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V; I_D = 4.8 A[b]	-	-	0.85	Ω
Forward Transconductance	g_{fs}	V_{DS} = 50 V, I_D = 4.8 A[b]	4.0	-	-	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5	-	1100	-	pF
Output Capacitance	C_{oss}		-	170	-	
Reverse Transfer Capacitance	C_{rss}		-	18	-	
Total Gate Charge	Q_g	V_{GS} = 10 V; I_D = 8.0 A, V_{DS} = 400 V see fig. 6 and 13[b]	-	-	39	nC
Gate-Source Charge	Q_{gs}		-	-	10	
Gate-Drain Charge	Q_{gd}		-	-	19	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 250 V, I_D = 8.0 A, R_g = 9.1 Ω, R_D= 30 Ω see fig. 10[b]	-	12	-	ns
Rise Time	t_r		-	25	-	
Turn-Off Delay Time	$t_{d(off)}$		-	27	-	
Fall Time	t_f		-	19	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	8.0	A
Pulsed Diode Forward Current[a]	I_{SM}		-	-	28	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = 8.0 A, V_{GS} = 0 V[b]	-	-	2.0	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = 8.0 A, dI/dt = 100 A/μs[b]	-	490	740	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	3.0	4.5	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

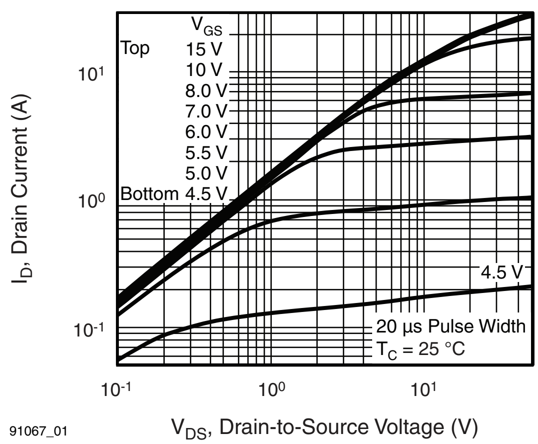


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

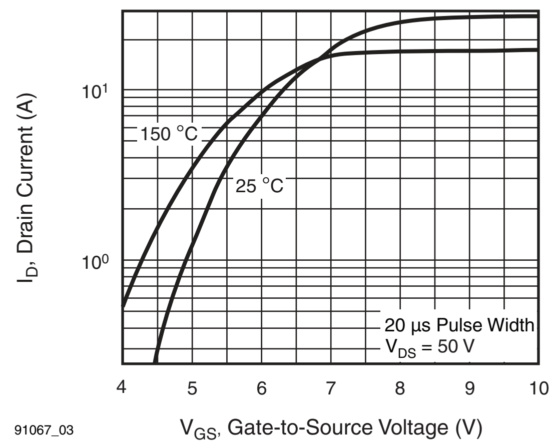


Fig. 3 - Typical Transfer Characteristics

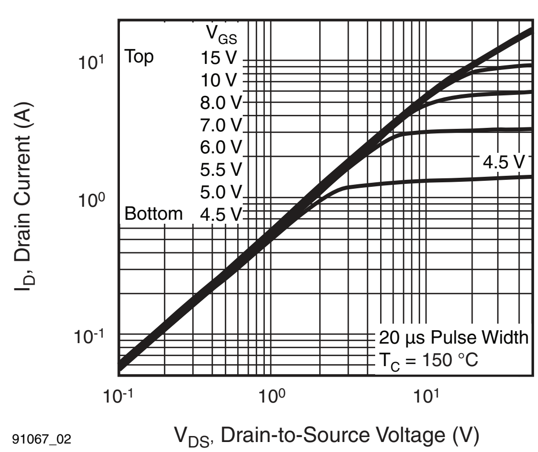


Fig. 2 - Typical Output Characteristics, T_C = 150 °C

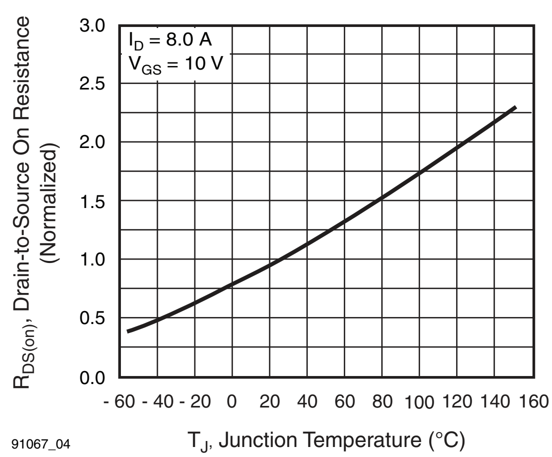


Fig. 4 - Normalized On-Resistance vs. Temperature

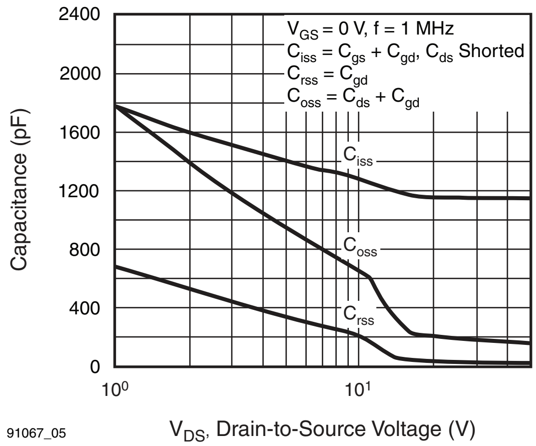


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

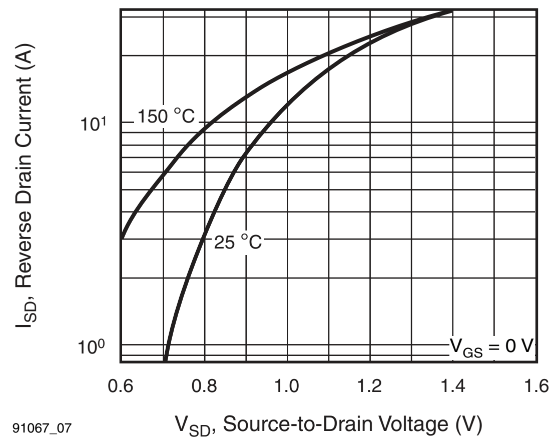


Fig. 7 - Typical Source-Drain Diode Forward Voltage

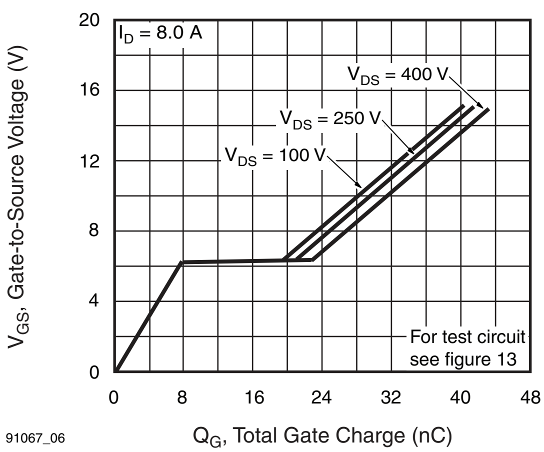


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

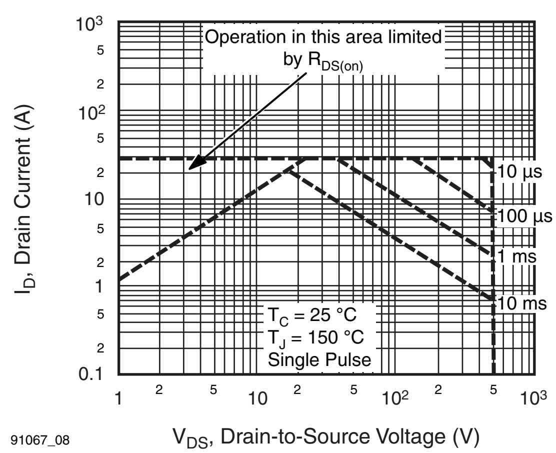


Fig. 8 - Maximum Safe Operating Area

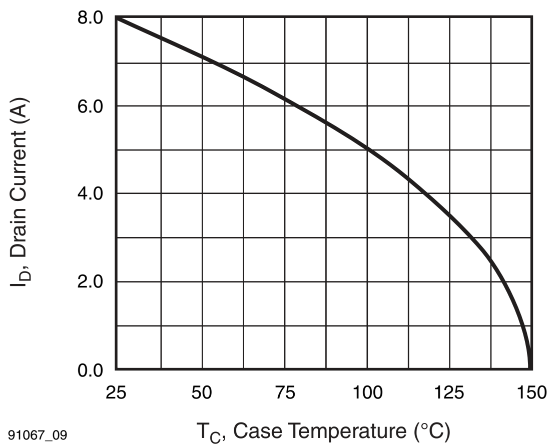


Fig. 9 - Maximum Drain Current vs. Case Temperature

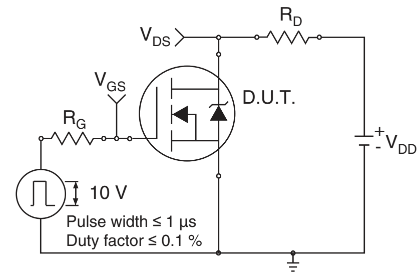


Fig. 10a - Switching Time Test Circuit

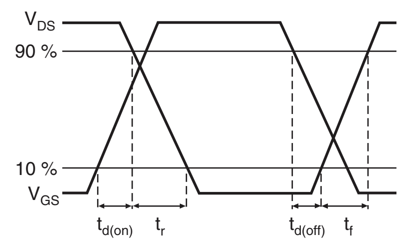


Fig. 10b - Switching Time Waveforms

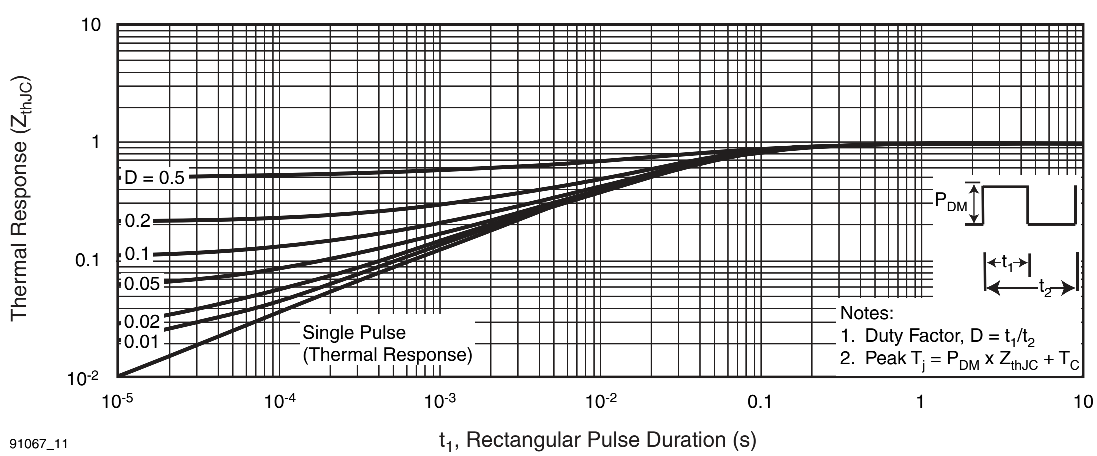


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

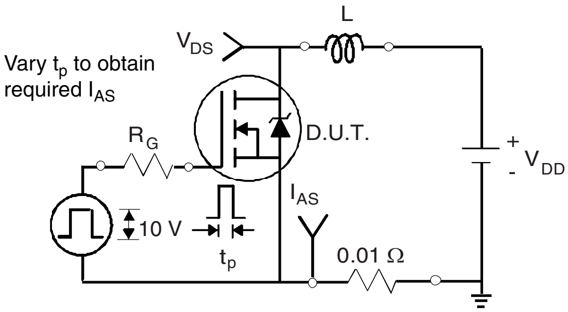


Fig. 12a - Unclamped Inductive Test Circuit

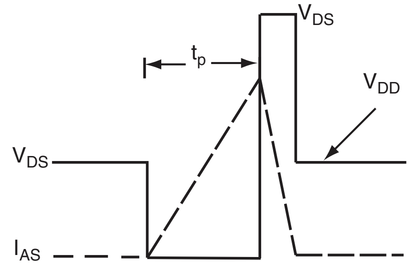


Fig. 12b - Unclamped Inductive Waveforms

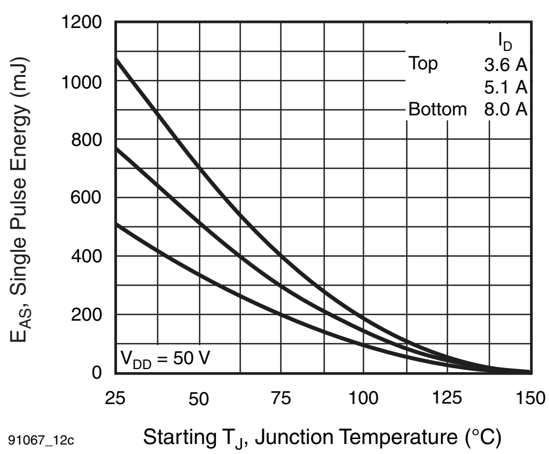


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

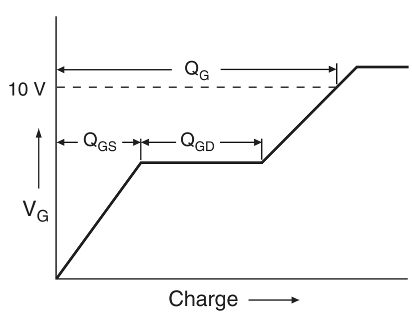


Fig. 13a - Basic Gate Charge Waveform

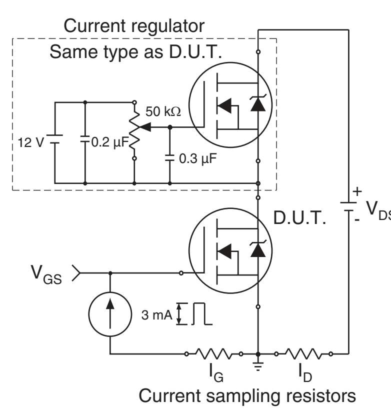
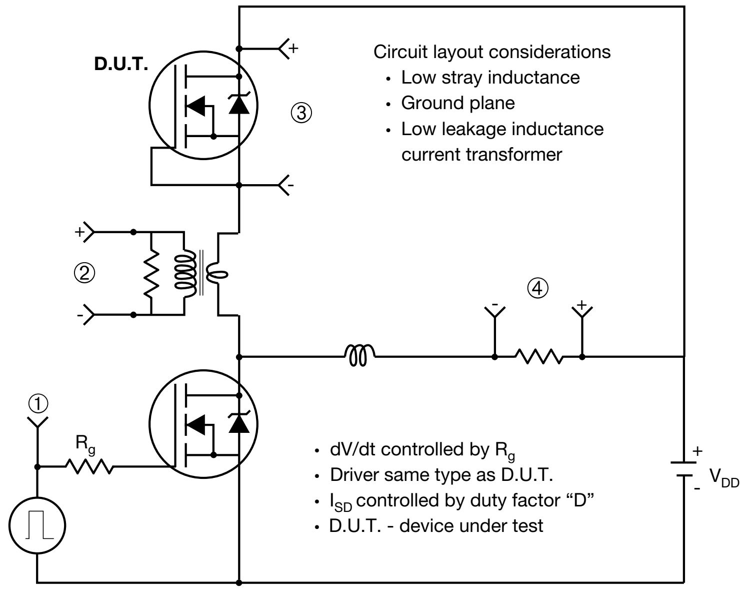
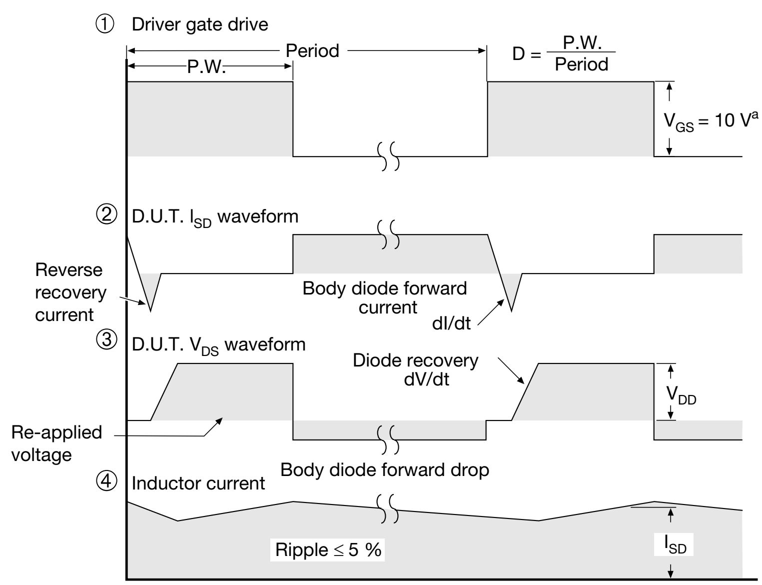


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit





Note

a. V_{GS} = 5 V for logic level devices

Fig. 14 - For N-Channel

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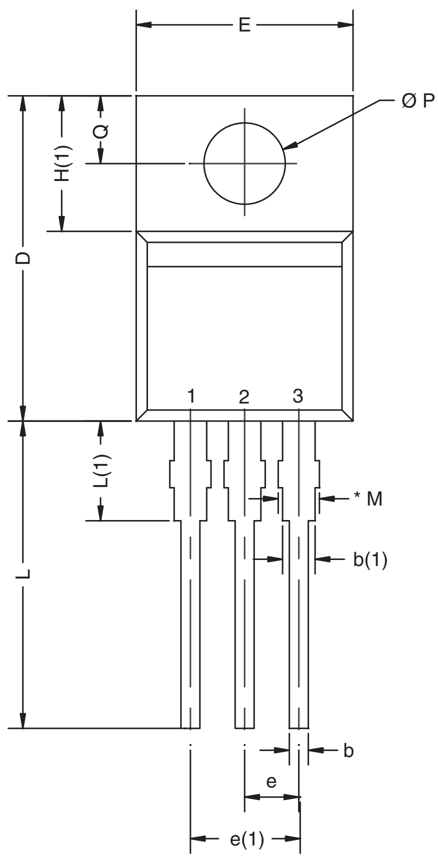

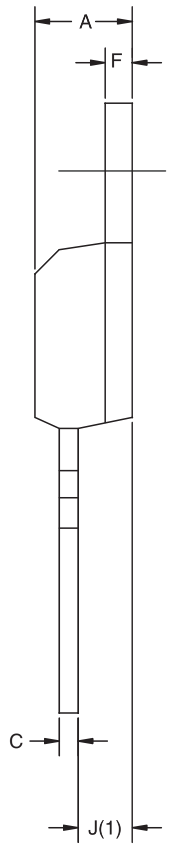

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: X10-0416-Rev. M, 01-Nov-10 DWG: 5471				

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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